

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

SC1006-01LTG-MS

Product specification

Features

- 2-pin lead-less package
- Junction capacitance (Type. value: 80pF)
- Peak Pulse current (8/20μs) Max:8A
- IEC61000-4-2 (ESD) ±30kV (air), ±30kV (contact)
- Low clamping voltage
- Low leakage current
- Working voltages:5V
- RoHS Compliant

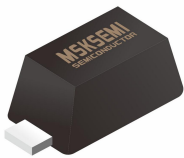
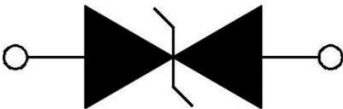
Mechanical Characteristics

- Package: SOD-523
- Lead Finish:Matte Tin
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation,Digital Cameras
- Peripherals, Audio Players, Industrial Equipment

Reference News

SOD-523	Graphic symbol	Marking
	 Bi-directional	

Absolute Maximum Ratings (T=25°C, RH=45%-75%, unless otherwise noted)

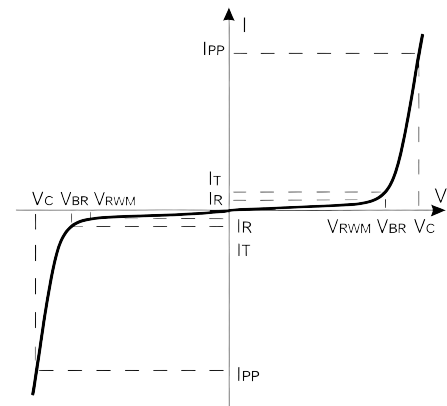
Parameters	Symbol	Value	Unit
Peak Pulse Power (tp=8/20μs waveform)	P _{PP}	128	W
Peak Pulse Current (8/20μs)	I _{PP}	8	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±30 ±30	KV
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Electrical characteristics (TA=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V _{RWM}				5	V
Reverse Breakdown Voltage	V _{BR}	I _R = 1mA	5.6		8	V
Reverse Leakage Current	I _R	V _R = 5V			0.2	uA
Clamping voltage	V _C	I _{PP} = 1A, T _p =8/20us			10	V
Clamping voltage	V _C	I _{PP} = 8A, T _p =8/20us		12	16	V
Junction capacitance	C _J	V _R =0V, f =1MHz		80	100	pF

Electronics Parameter

Symbol	Parameter
V _{RWM}	Peak Reverse Working Voltage
I _R	Reverse Leakage Current @V _{RWM}
V _{BR}	Breakdown Voltage @I _T
I _T	Test Current
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage@I _{PP}
P _{PP}	Peak Pulse Power



Typical Characteristics

FIG1: Power rating derating curve

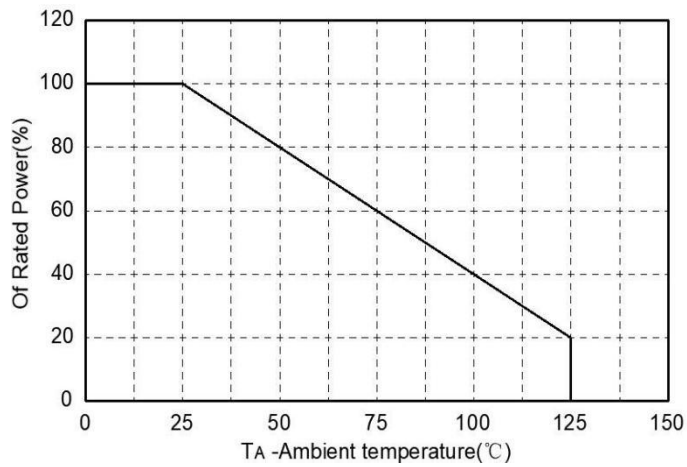


FIG2: pulse Waveform

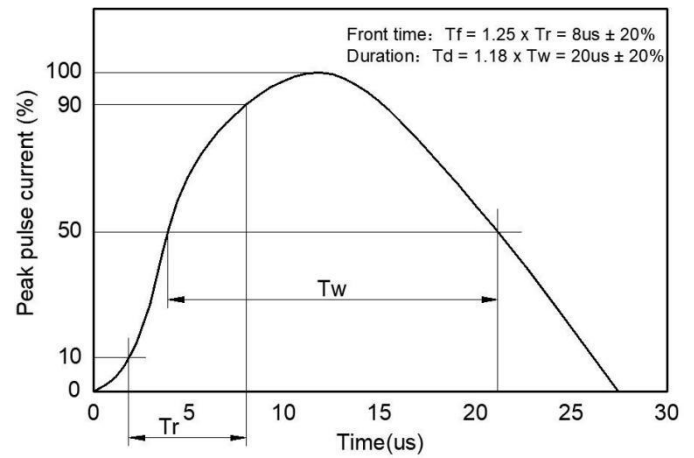


FIG3: Capacitance between terminals characteristics

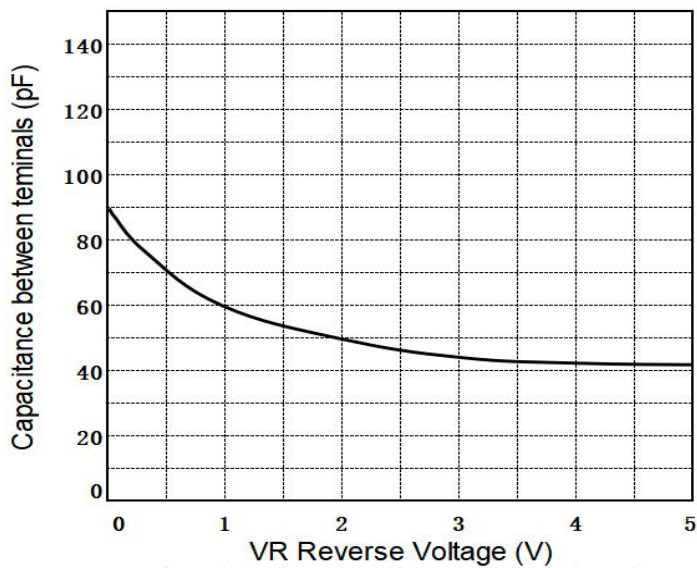
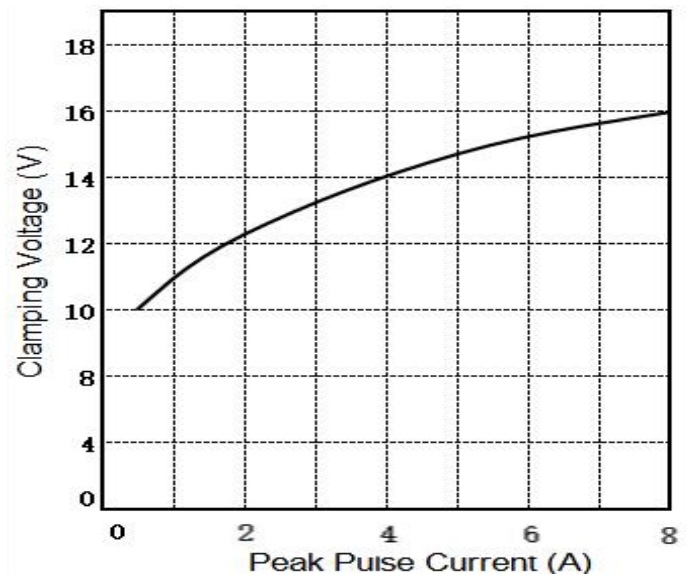
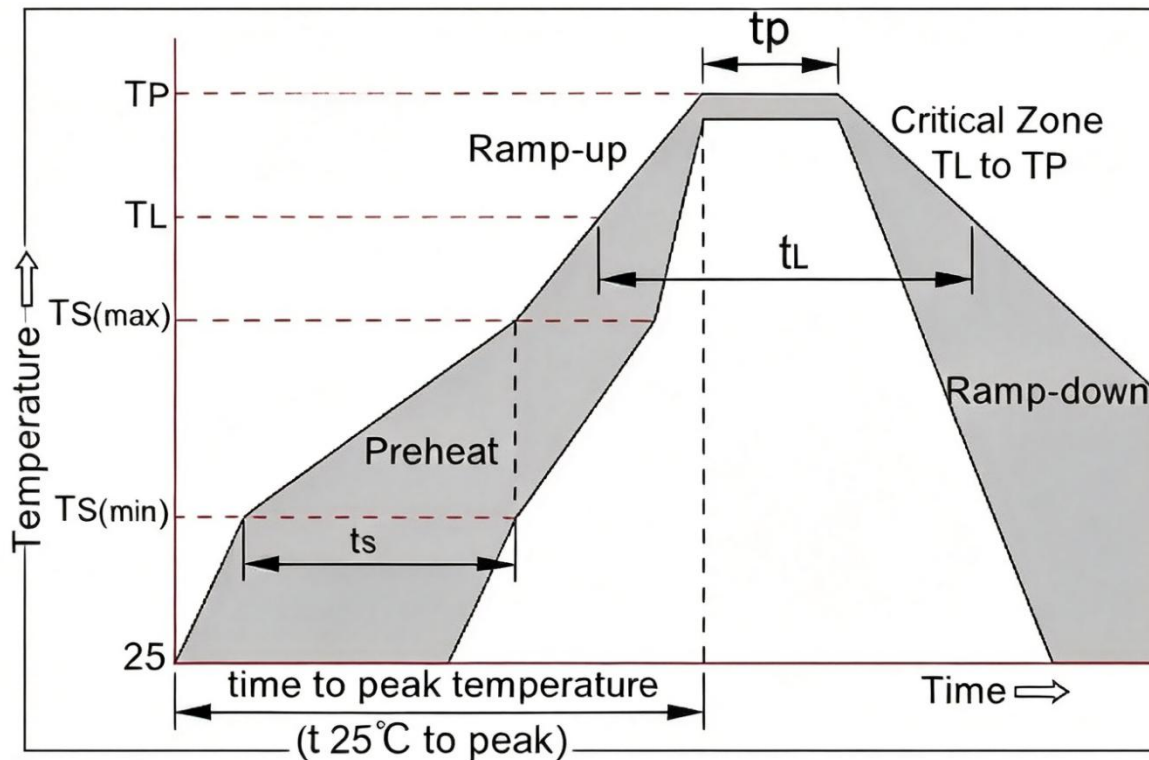


FIG4: Clamping Voltage vs. Peak Pulse Current

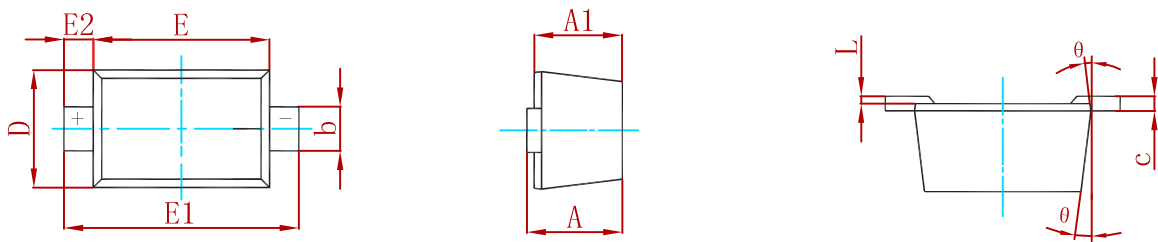


Soldering Parameters

Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

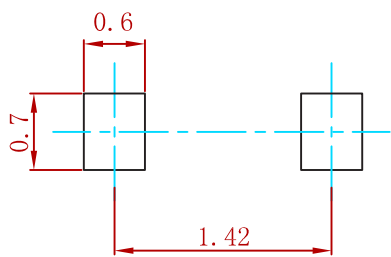


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.510	0.770	0.020	0.031
A1	0.500	0.700	0.020	0.028
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	0.750	0.850	0.030	0.033
E	1.100	1.300	0.043	0.051
E1	1.500	1.700	0.059	0.067
E2	0.200 REF		0.008 REF	
L	0.010	0.070	0.001	0.003
θ	7° REF		7° REF	

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SC1006-01LTG-MS	SOD-523	3000

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